



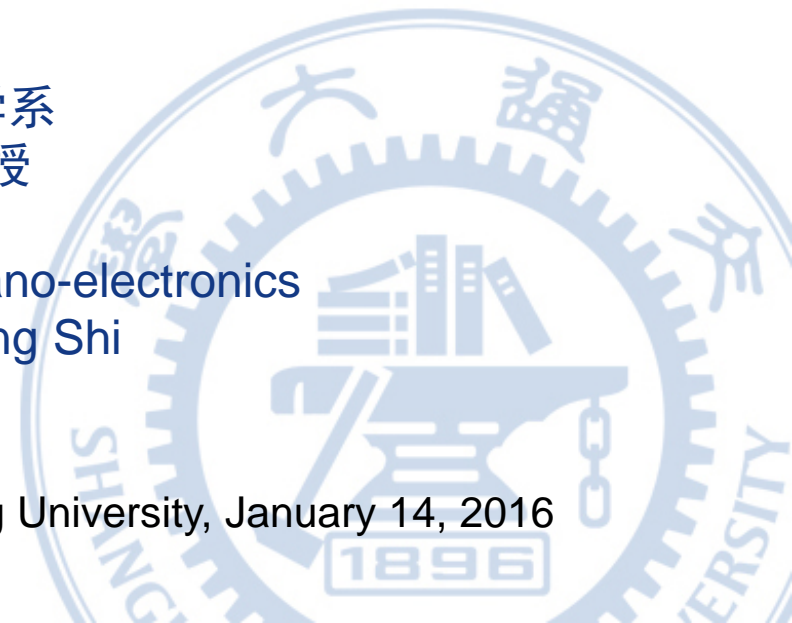
模拟集成电路符号化低阶模型 自动生成方法与应用

Automatic Generation Method of Low-order Models for Analog Integrated Circuits with Applications

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Master Degree Defense, Shanghai Jiao Tong University, January 14, 2016



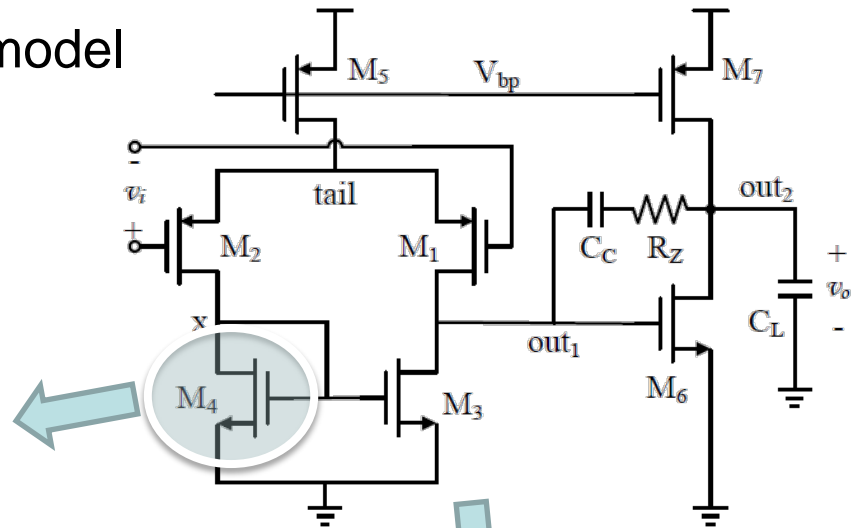
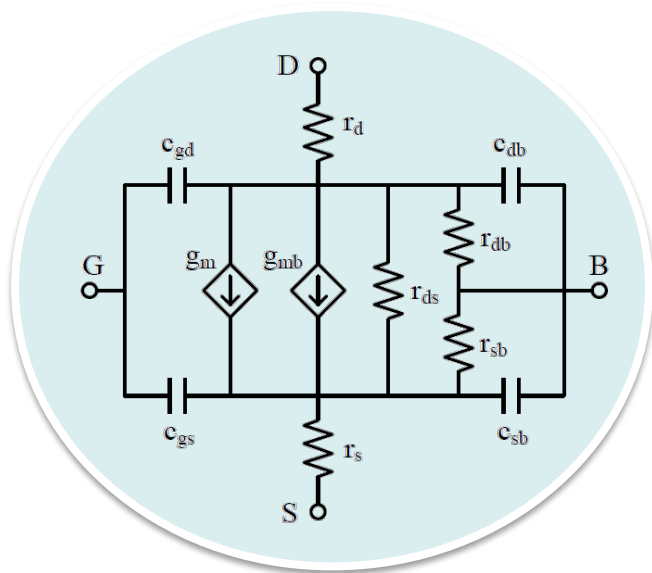
Outline

- ① Research motivation
- ① Background review
- ① **Main contribution**
 - Topology simplification algorithm
 - Applications (Time-domain & CMRR/PSRR)
- ① Experimental results
- ① Conclusion

Motivation for Model Order Reduction

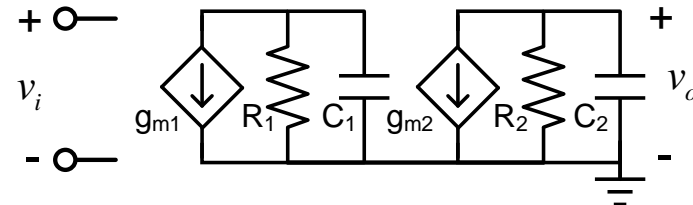
State of Art in Analog Circuit Design

High-order model



How to generate?

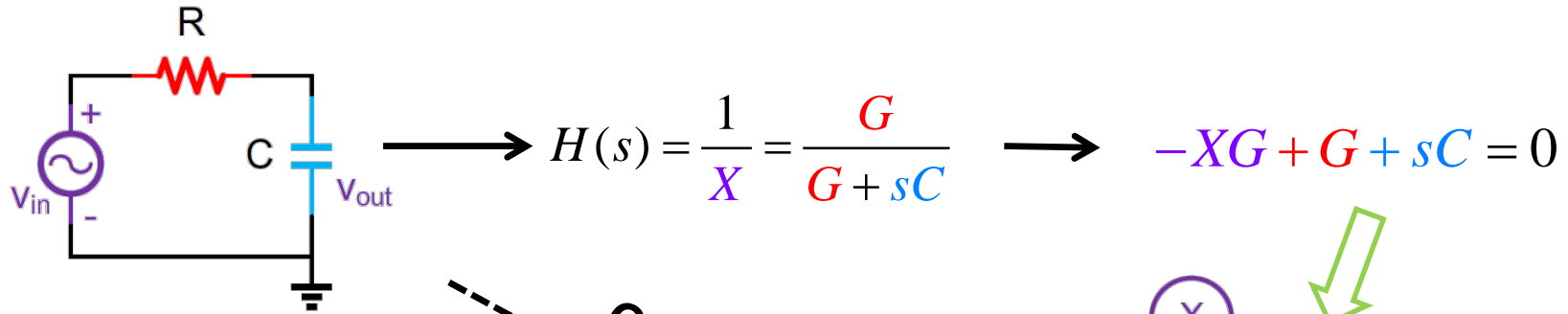
Low-order model



Hard to capture principal elements in analog circuits

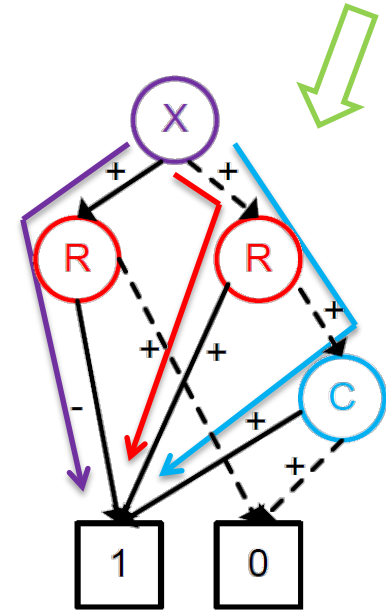
Symbolic Analysis

- Graph-Pair Decision Diagram – A BDD-Based Structure
- A topology-based analysis method



Construct

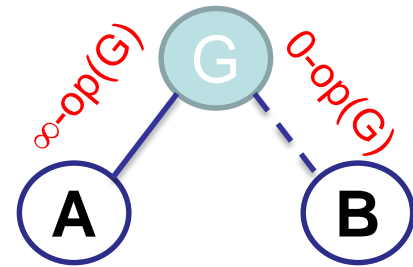
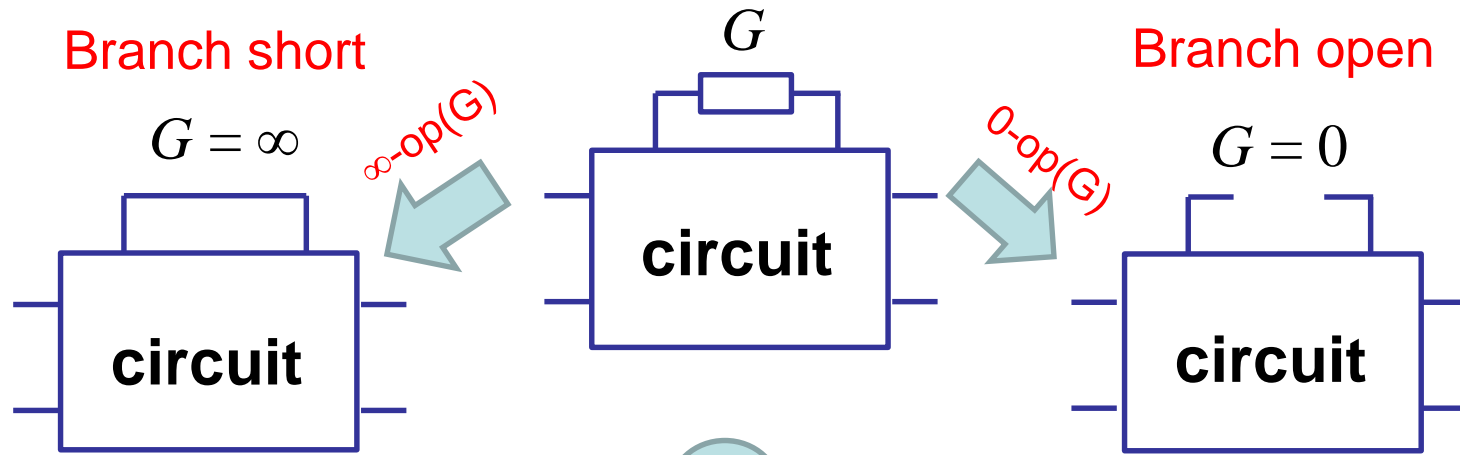
This diagram actually encodes the circuit topology



1-paths in the GPDD are symbolic terms

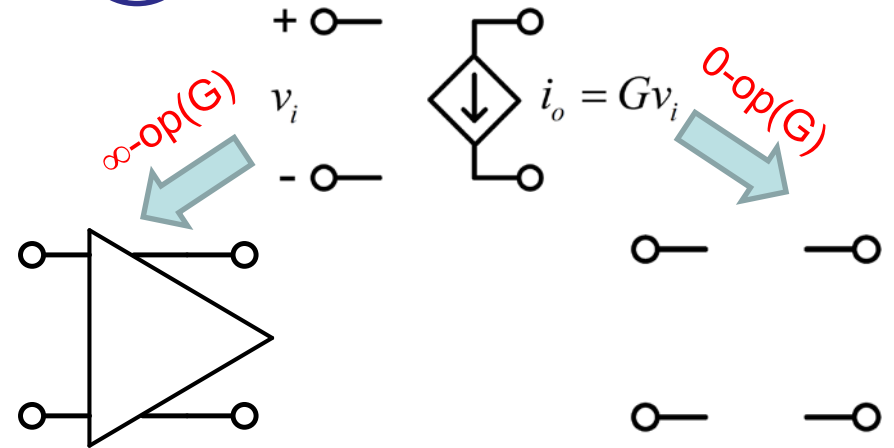
G. Shi (TCAD, 2013)

Two Operations for Topology Reduction in GPDD



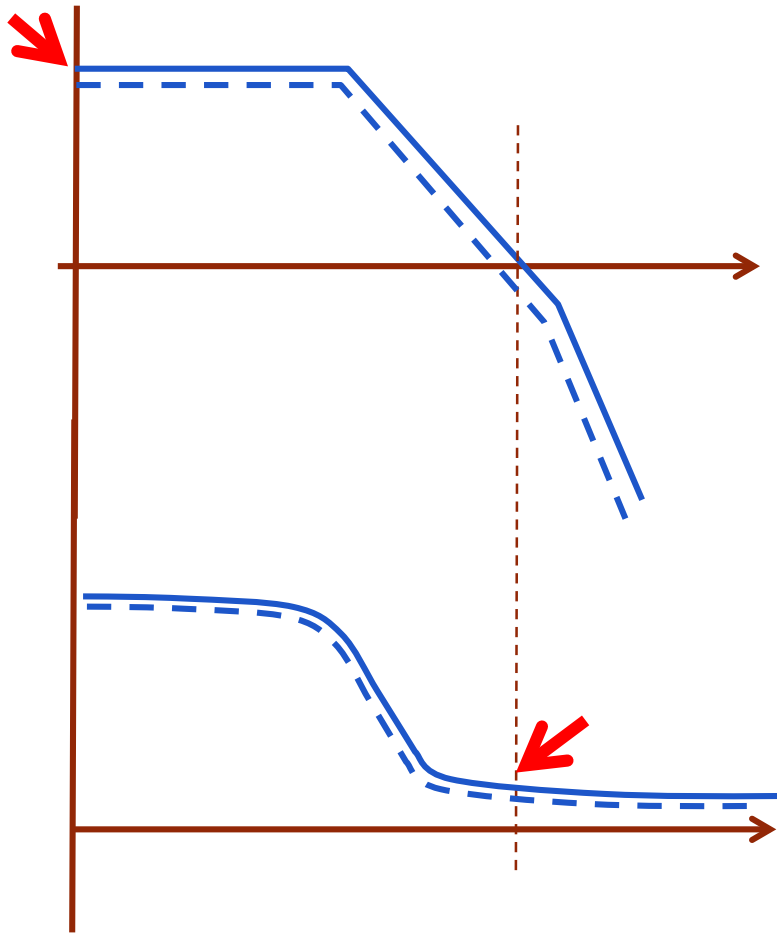
Admissible elements:
 VCVS / CCCS / **VCCS** / CCVS

↑
 R / L / C



Significance Definition

- Significance from two operations



Fitness at ∞ -op

$$F_{\infty-op} = \sqrt{\text{Rel. Gain Err.}_{\infty-op}^2 + \text{Rel. PM Err.}_{\infty-op}^2}$$



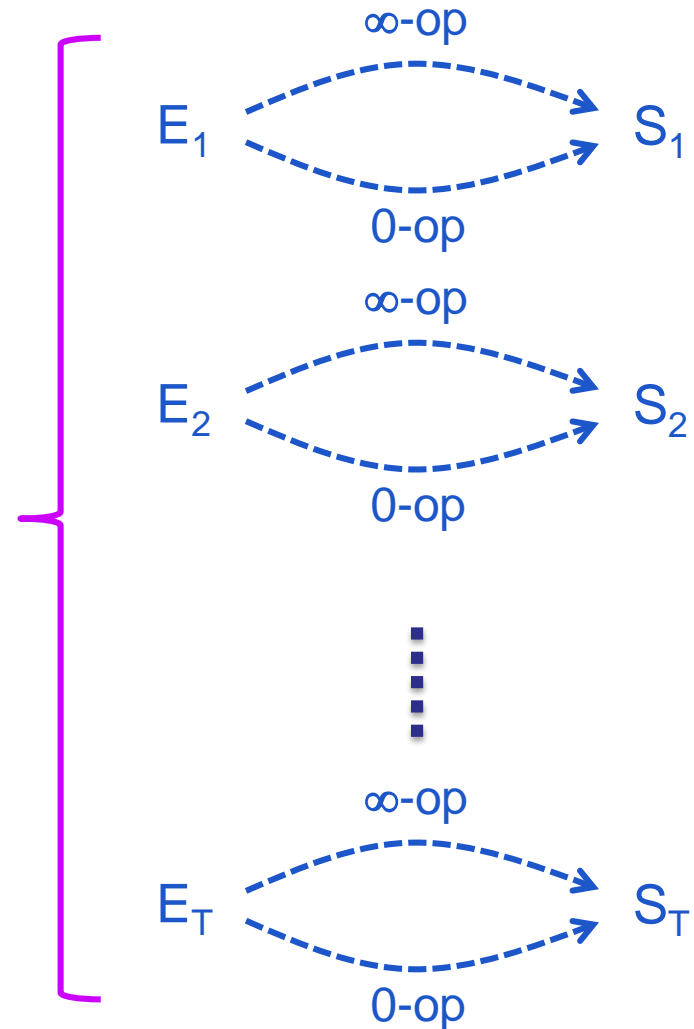
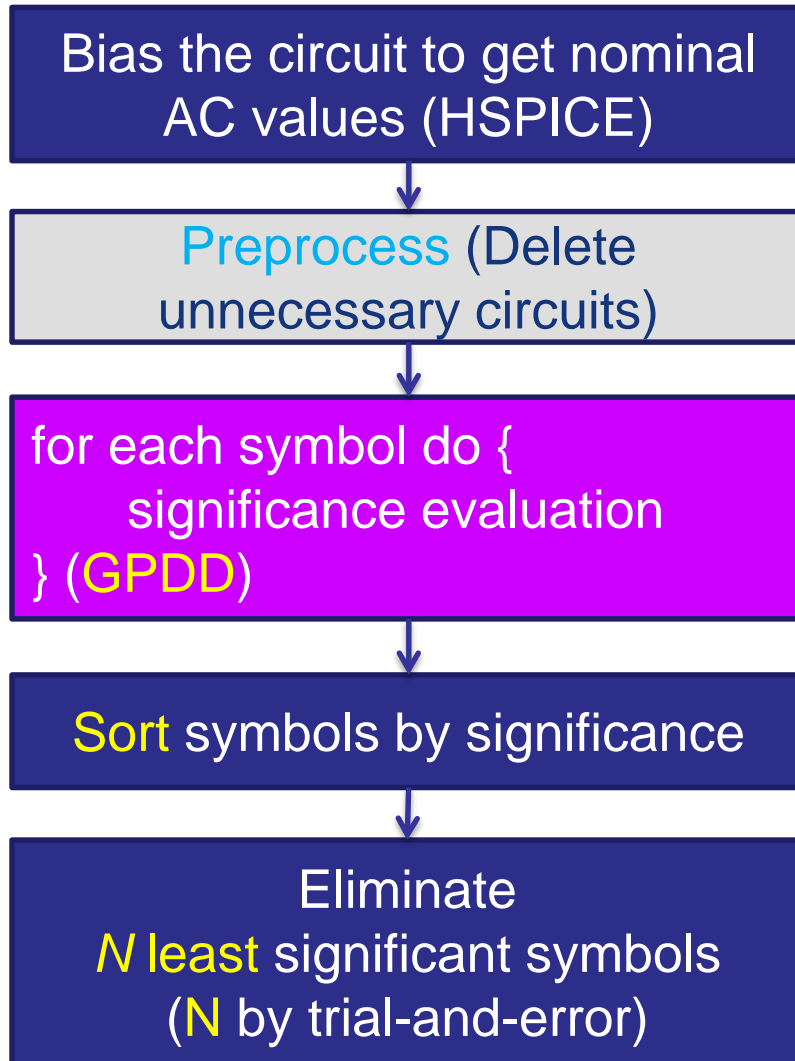
Significance: $S = \min \{ F_{\infty-op}, F_{0-op} \}$



Fitness at 0-op

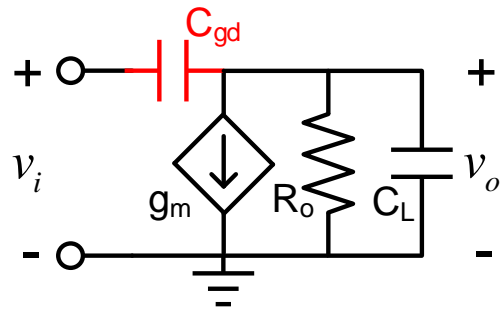
$$F_{0-op} = \sqrt{\text{Rel. Gain Err.}_{0-op}^2 + \text{Rel. PM Err.}_{0-op}^2}$$

Low-order Model Procedure



Example

Significance calculation

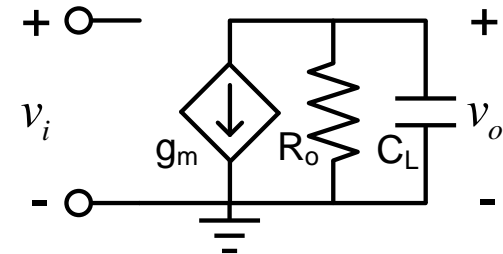


$$C_{gd} = 50 \text{ fF}$$

$$g_m = 1 \text{ mS}$$

$$R_o = 100 \text{ k}\Omega$$

$$C_L = 1 \text{ pF}$$

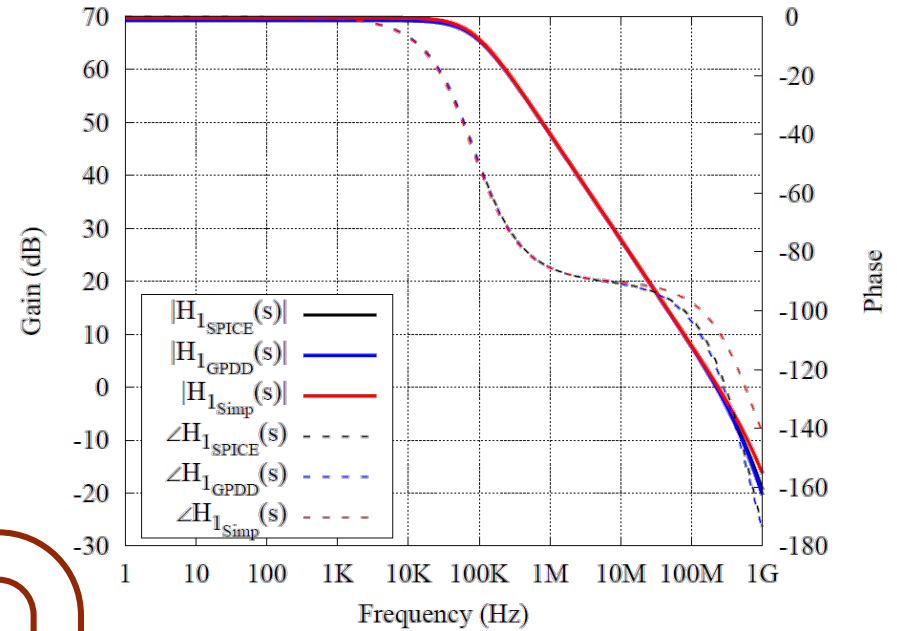
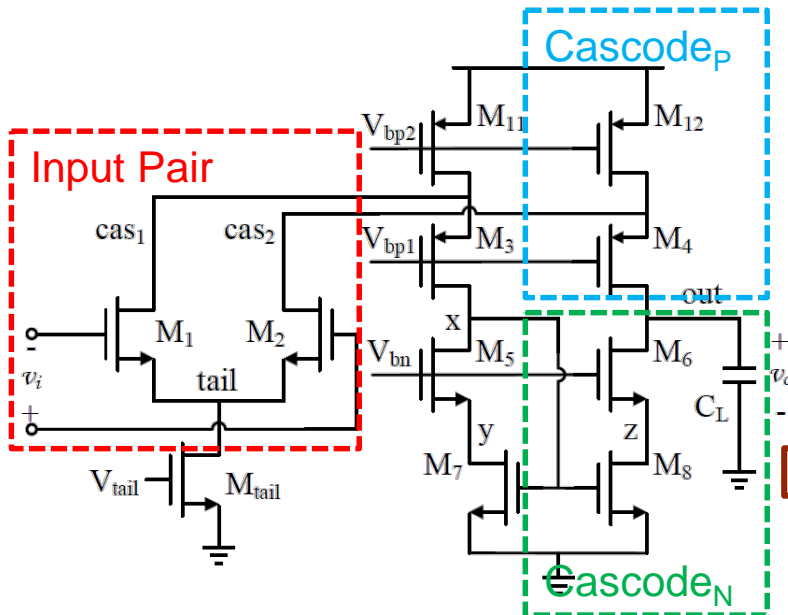


Symbol	Operation	ε	$\varepsilon_{\infty\text{-op}}$	$\varepsilon_{0\text{-op}}$
C_{gd}	0-op	3.28e-02	1.41e+00	3.28e-02
C_L	0-op	1.23e-01	Inf / NaN	1.23e-01
R_o	0-op	3.09e+00	Inf / NaN	3.09e+00
g_m	0-op	4.85e+00	Inf / NaN	4.85e+00

Process abnormal value

Test Circuit 1

Folded-cascode opamp

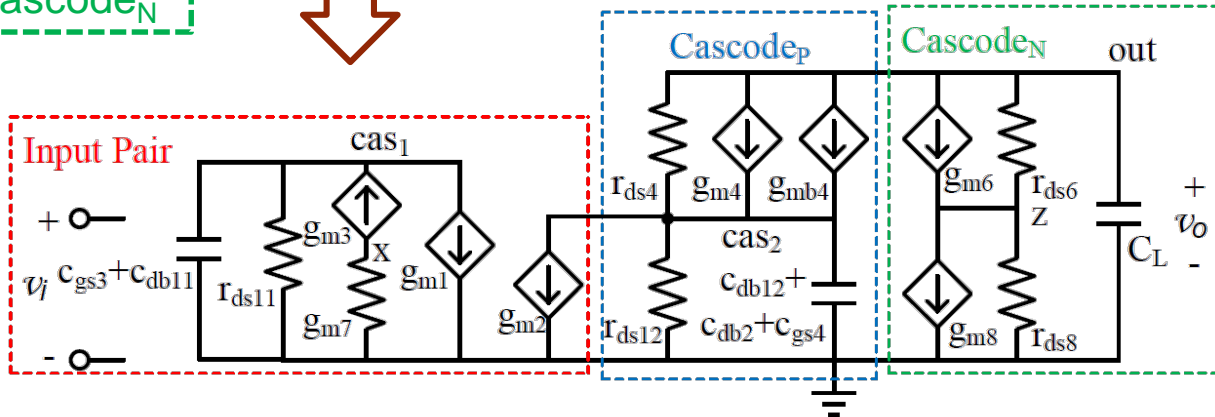


$$A_v = G_m R_o = -g_{m1} \left[(R_{out,4}) \parallel (R_{out,6}) \right]$$

$$R_{out,4} = \left[g_{m4} (r_{ds2} \parallel r_{ds12}) \right] r_{ds4}$$

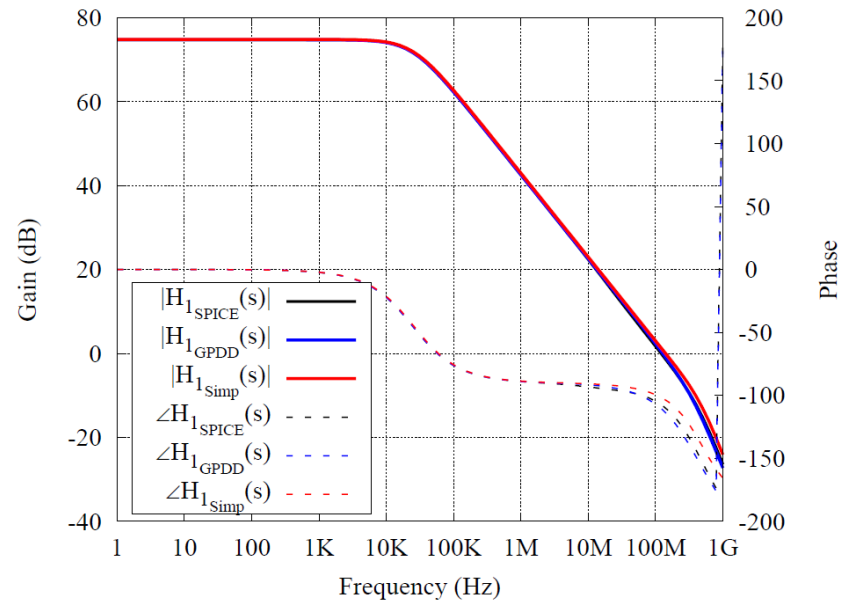
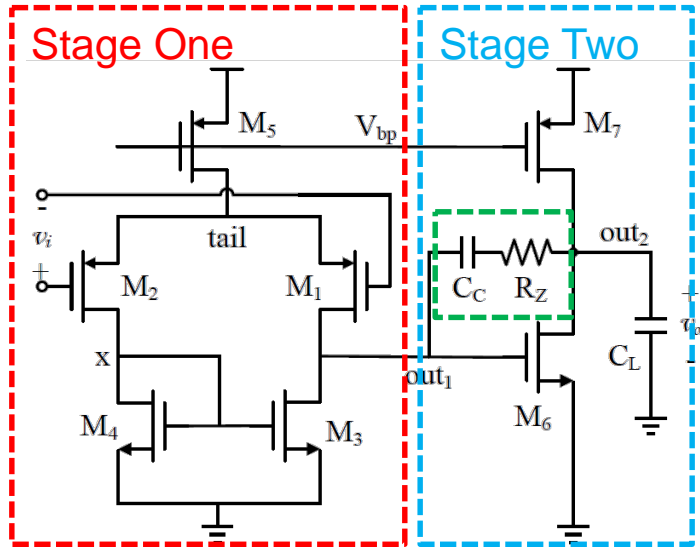
$$R_{out,6} = (g_{m6} r_{ds8}) r_{ds6}$$

Matches textbook result!



Test Circuit 2

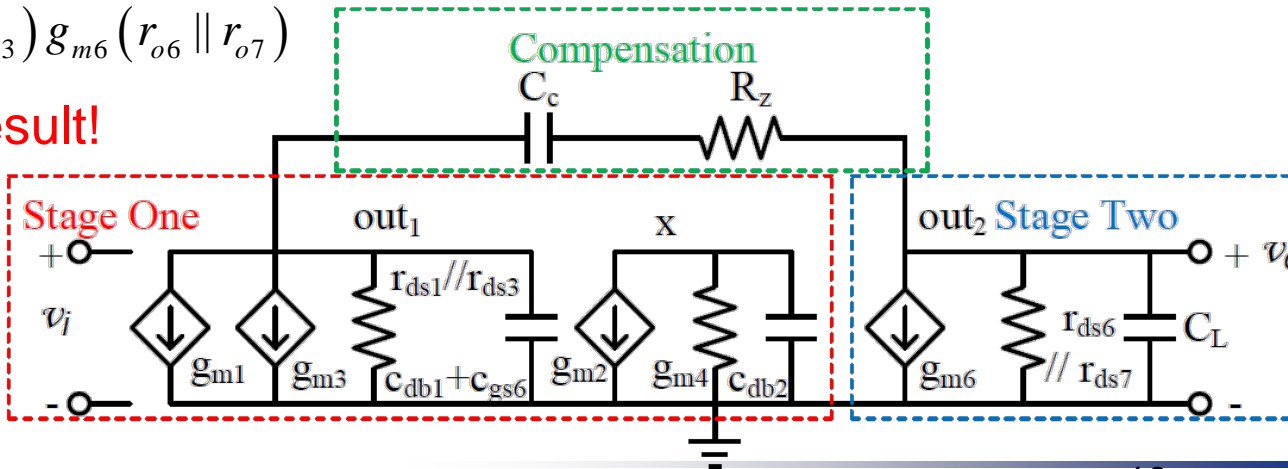
Two-stage opamp



Simplified circuit

$$A_v = A_{v1} A_{v2} = -g_{m1} (r_{o1} \parallel r_{o3}) g_{m6} (r_{o6} \parallel r_{o7})$$

Matches textbook result!



Poles & Zeros Results

- ⊕ Poles & Zeros comparison for two-stage opamp

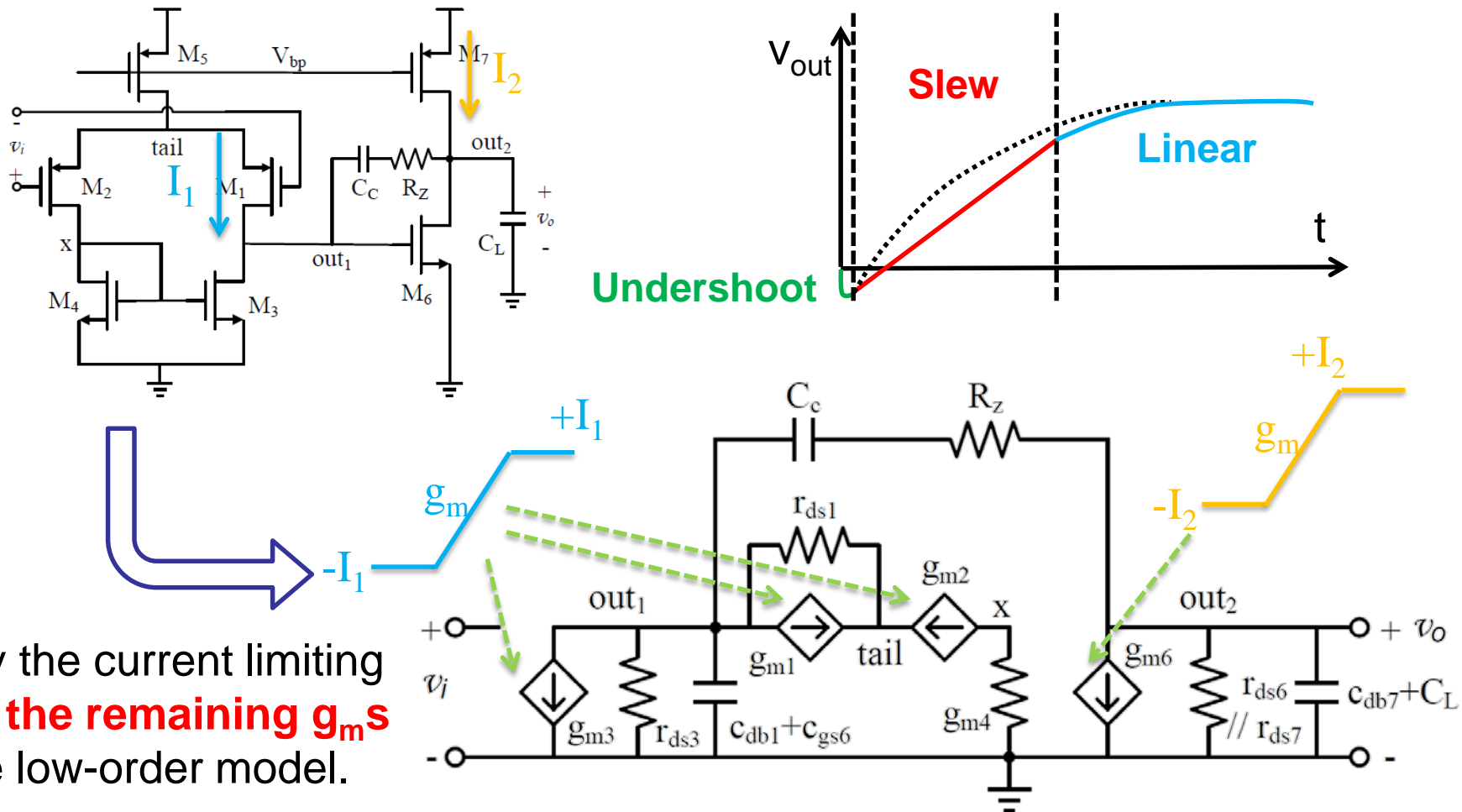
Type	Original Circuit (Hz)	Low-order Model (Hz)
Poles	-24.6K	-25.6KHz
	-19.4M	
	-374.1M ± 65.1M	-375.8MHz
Zeros	-21.2M	
	-298.0M	-298.1M

- ⊕ Model order comparison

Circuit Types	Original Circuits		Low-order Models	
	# poles	# zeros	# poles	# zeros
Folded-Cascode	9	8	3	1
2-stage with nulling resistor	6	6	4	2
2-stage with voltage buffer	6	6	3	2
2-stage with current buffer	7	7	4	2

Time-Domain Model Review

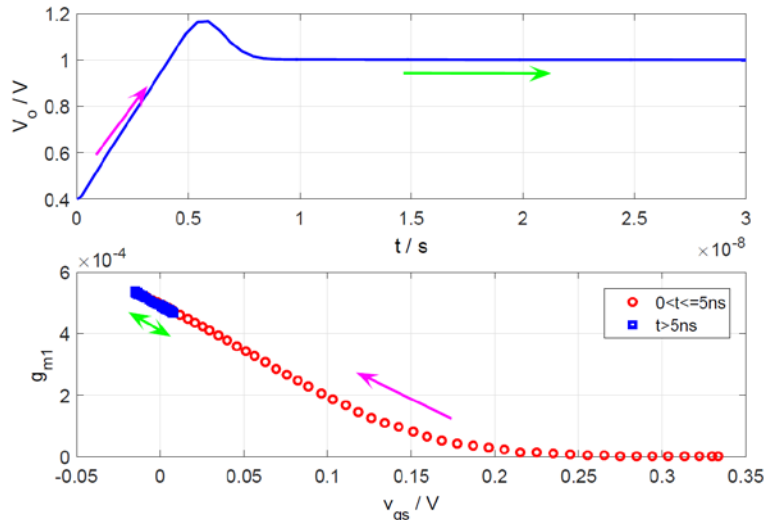
⊙ Slew-Settling Behavior



Apply the current limiting to **all the remaining g_m s** in the low-order model.

Nonlinear Function Selection

Varying gm during the slew process



For previous works on slew-settling model, g_m was assumed zero during the **entire slewing period**. Actually, g_m **hikes gradually** as the MOSFET gate-source voltage rises by degrees.

$$S_0(x) = \begin{cases} 1 & x \geq 1 \\ x & -1 \leq x < 1 \\ -1 & x < -1 \end{cases}$$

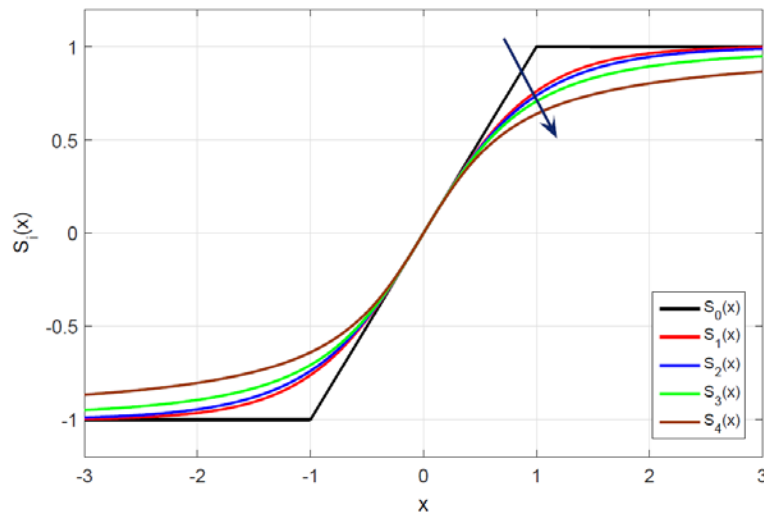
$$S_1(x) = \tanh(x)$$

$$S_2(x) = \frac{2}{\pi} gd \left(\frac{\pi}{2} x \right) = \frac{2}{\pi} \arcsin \left(\tanh \left(\frac{\pi}{2} x \right) \right)$$

$$S_3(x) = \frac{x}{\sqrt{1+x^2}}$$

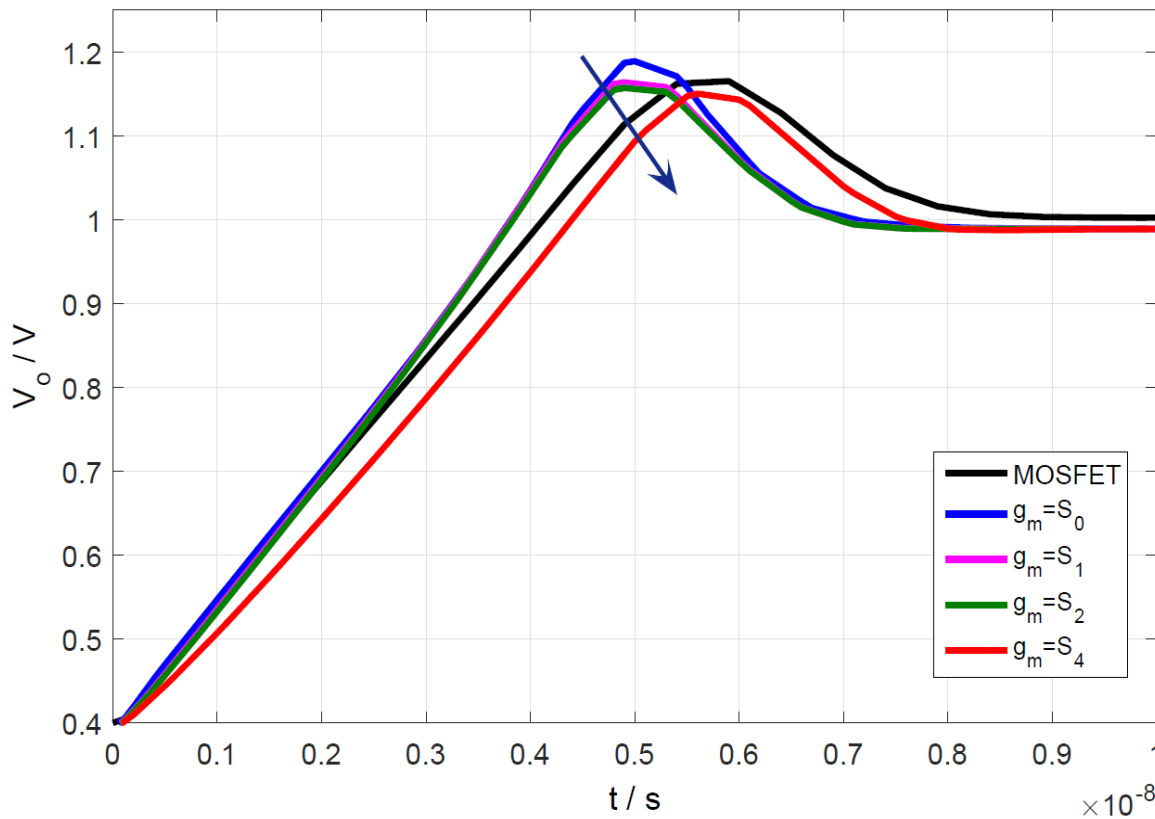
$$S_4(x) = \frac{2}{\pi} \arctan \left(\frac{\pi}{2} x \right)$$

Sigmoid Function



Experimental Results

Output voltage with different sigmoid functions



The arrow exhibits the **same order** as shown in the previous slide.

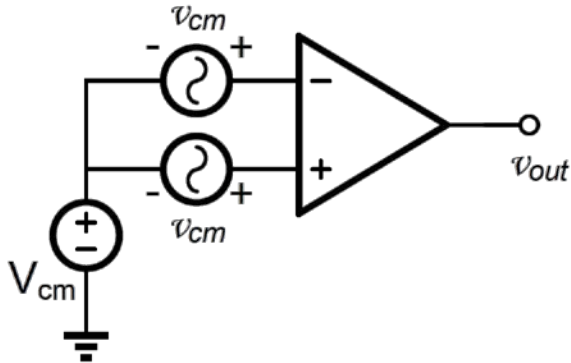
S_0 , S_1 , S_2 all have better performance in **slew rate estimation**, however, S_4 has a good agreement with transistor-level simulation in **settling time prediction**.

S_3 is promising in both regions, but S_3 **can't converge** in HSPICE simulation.

CMRR/PSRR Analysis

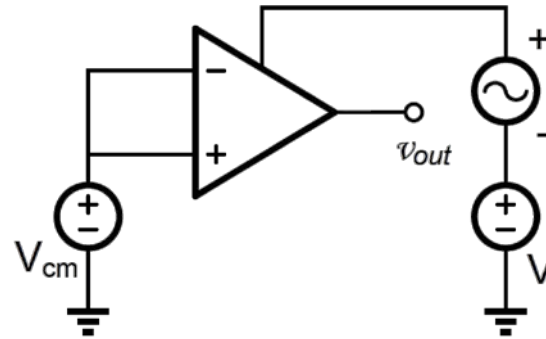
Introduction to CMRR & PSRR

CMRR: Common Mode Rejection Ratio PSRR: Power Supply Rejection Ratio



$$A_{CM} = \frac{v_{out}}{v_{cm}}$$

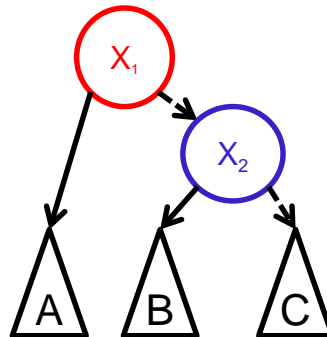
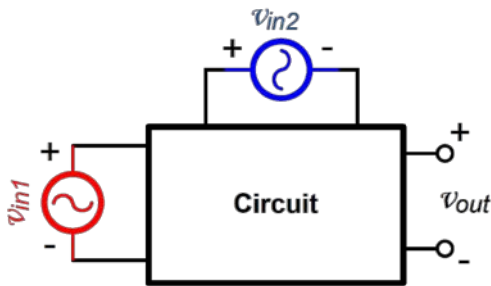
$$CMRR = \frac{A_v}{A_{CM}}$$



$$A_{DD} \Big|_{v_{in}=0} = \frac{v_{out}}{v_{dd}}$$

$$PSRR = \frac{A_v \Big|_{v_{dd}=0}}{A_{DD} \Big|_{v_{in}=0}}$$

GPDD Multiport Construction



$$H_1(s) = \frac{f_A(A)}{f_C(C)}$$

$$H_2(s) = \frac{f_B(B)}{f_C(C)}$$

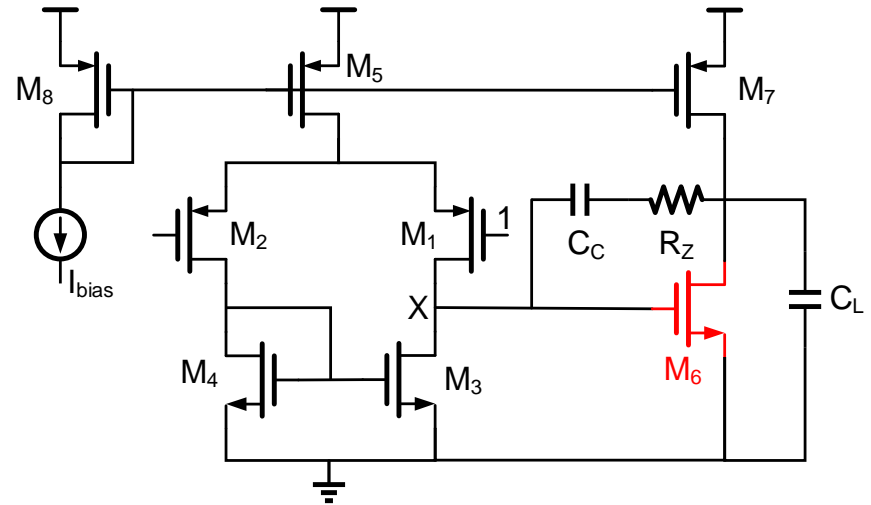
Multi-port Analysis for Opamp Sizing

W₆ Sizing

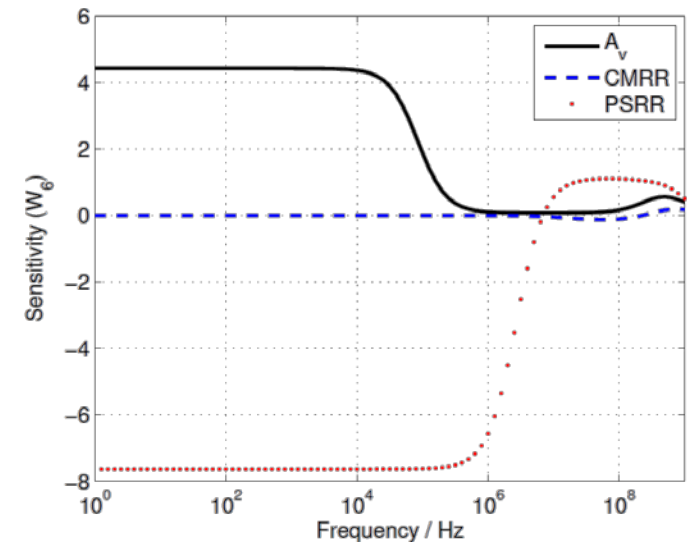
$$\text{Sens}(|H(s)|, W_6) > 0 \rightarrow W_6 \uparrow \Rightarrow |H(s)| \uparrow$$

$$\text{Sens}(|H(s)|, W_6) < 0 \rightarrow W_6 \uparrow \Rightarrow |H(s)| \downarrow$$

$$\text{Sens}(|H(s)|, W_6) = 0 \rightarrow W_6 \updownarrow \Rightarrow |H(s)|$$



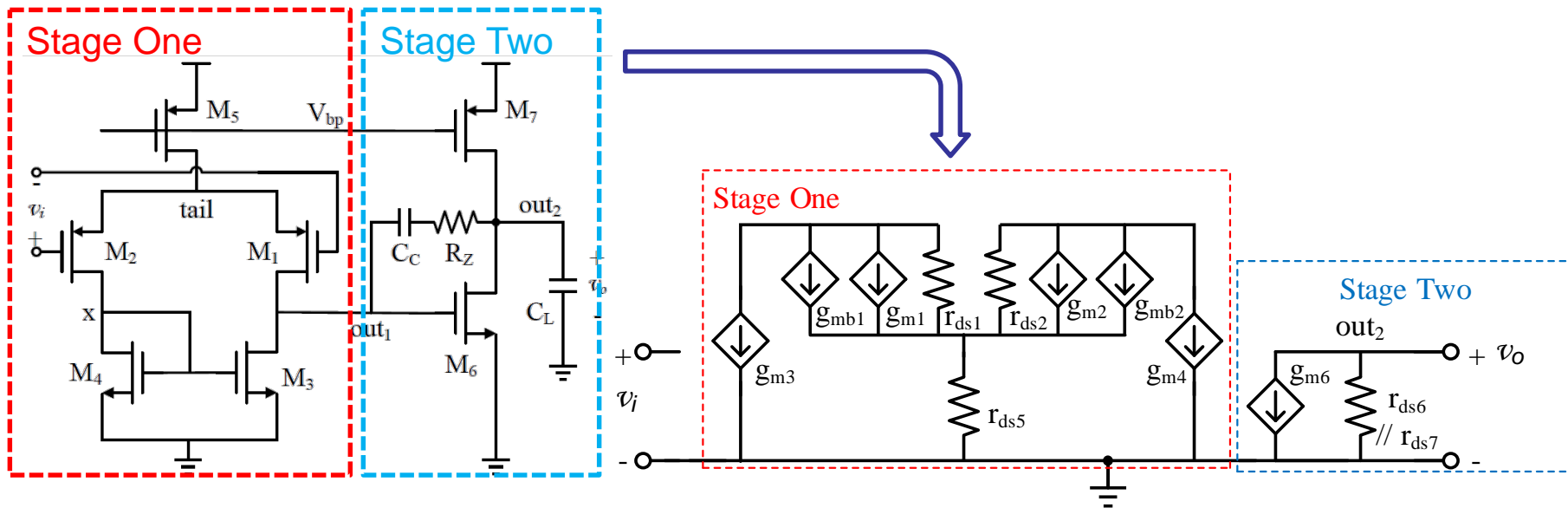
Sensitivity at DC	W ₆ =30um	W ₆ =31um	Improve
A _v	2.84K (69.1dB)	3.04K (69.7dB)	+7.04% (+0.6dB)
CMRR	2.07K (66.3dB)	2.07K (66.3dB)	+0% (+0dB)
PSRR	3.87K (71.8dB)	3.32K (70.4dB)	-14.2% (-1.4dB)
Sens(A _v , W ₆)	4.43	-0.20	-
Sens(CMRR, W ₆)	6.1e-8	9.4e-8	-
Sens(PSRR, W ₆)	-7.63	-2.83	-



Model Generation for Common Mode Gain

- Same procedure applied to common-mode gain A_{cm}
- Significance Selection (Only consider A_{cm} for now)

Original A_{cm}	Simplified A_{cm}
3.99dB	4.07dB



Conclusion

- ⊗ GPDD symbolic construction can be applied to **topological circuit reduction**.
- ⊗ Can automatically generate small-signal model as **behavioral model** for system-level use.
- ⊗ Extended to generate **large-signal model** for slew-settling analysis
- ⊗ Explored the possibility for **multi-port model** generation on GPDD.

Thanks!
Q & A